

Remarks

Reconsideration of the above-identified application is requested in view of the remarks that follow.

On June 10, 2005, Applicant filed a response to the January 13, 2005, Office Action in this application. On June 16, 2005, the PTO issued a Notice of Non-Compliant Amendment (37 CFR 1.121), requiring that Applicant provide proper status identifiers for the claims amended in the June 10 response. As indicated above, amended claims are now identified as "Currently Amended" as suggested in the June 16 PTO Notice.

In the January 13, 2005 Office Action in this application, the Examiner objected to the specification, stating that the wording "The amount of current flowing between the source 110 and the drain 112 is proportional to the amount of resistance of the channel region 116" is unsupported by the specification.

As indicated above, the wording cited by the Examiner has been deleted from the specification, without prejudice.

The Examiner has rejected original claims 1-8 under 35 U.S.C. 103(a) as being unpatentable over the Choi et al. reference in view of the Ichikawa reference. In so doing, the Examiner states that it would be obvious to a person skilled in the art to modify the Choi et al. MOSFET transistor structure to provide Applicant's claimed invention.

As indicated above, Applicant has amended original independent MOSFET transistor structure claim 1 and original independent method claim 7 to more clearly define the invention. Specifically, language has been added to both independent claim 1 and independent claim 7 to clarify that the active region formed in the substrate of the semiconductor material is substantially rectangular, thereby defining a substantially rectangular interface between the active region and the isolation dielectric material. Both claim 1 and claim 7 then further recite that conductive gate is formed to include a first portion that extends over the substrate channel region of the MOSFET transistor and second portion that extends continuously over the entire substantially rectangular perimeter interface between the isolation dielectric material and the active region.

Upon close review of the Choi et al. reference and the Ichikawa reference, Applicant submits that neither reference, whether considered individually or in combination, either teaches or suggests the formation of a MOSFET transistor conductive gate electrode that extends continuously over the entire substantially rectangular interface between isolation dielectric material and a substantially rectangular active device region for the MOSFET transistor.

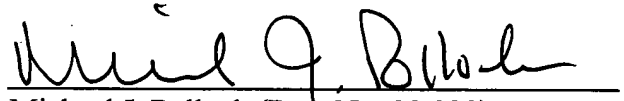
In view of the above, Applicant submits that all claims now present in this application patentably distinguish over the prior art. Therefore, it is requested that this application be pass to allowance.

Respectfully submitted,

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